

P-Channel 20-V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ.)
- 20	0.070 at $V_{GS} = - 5.0$ V	- 5.0	4.5 nC
	0.105 at $V_{GS} = - 2.5$ V	- 4.2	

SCHOTTKY PRODUCT SUMMARY

V_{KA} (V)	V_f (V) Diode Forward Voltage	I_F (A) ^a
20	0.45 at 1 A	2

FEATURES

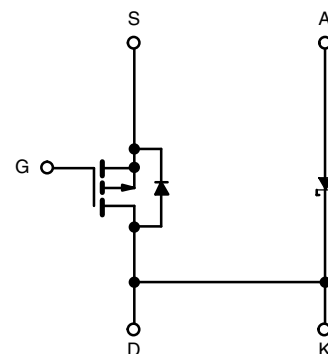
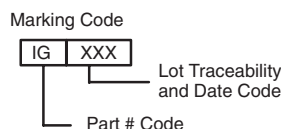
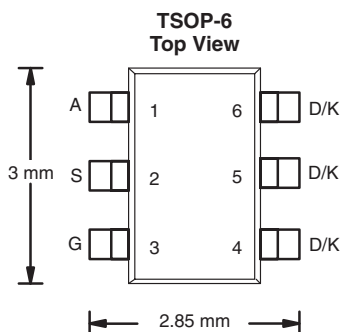
- Halogen-free According to IEC 61249-2-21 Definition
- LITTLE FOOT® Plus Schottky Power MOSFET
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- HDD
- DC-DC Converter
- Asynchronous Rectification



Ordering Information: Si3879DV-T1-E3 (Lead (Pb)-free)
Si3879DV-T1-GE3 (Lead (Pb)-free and Halogen-free)

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$, unless otherwise noted

Parameter		Symbol	Limit	Unit
Drain-Source Voltage (MOSFET)		V_{DS}	- 20	V
Reverse Voltage (Schottky)		V_{KA}	20	
Gate-Source Voltage (MOSFET)		V_{GS}	± 12	
Continuous Drain Current ($T_J = 150\text{ }^{\circ}\text{C}$) (MOSFET)	$T_C = 25\text{ }^{\circ}\text{C}$	I_D	- 5.0	A
	$T_C = 70\text{ }^{\circ}\text{C}$		- 4.0	
	$T_A = 25\text{ }^{\circ}\text{C}$		- 4.0 ^{b, c}	
	$T_A = 70\text{ }^{\circ}\text{C}$		- 3.0 ^{b, c}	
Pulsed Drain Current (MOSFET)		I_{DM}	- 20	
Continuous Source-Drain Diode Current (MOSFET Diode Conduction)	$T_C = 25\text{ }^{\circ}\text{C}$	I_S	- 2.7	
	$T_A = 25\text{ }^{\circ}\text{C}$		- 1.6 ^{b, c}	
Average Forward Current (Schottky)		I_F	2 ^b	
Pulsed Forward Current (Schottky)		I_{FM}	5	
Maximum Power Dissipation (MOSFET)	$T_C = 25\text{ }^{\circ}\text{C}$	P_D	3.3	W
	$T_C = 70\text{ }^{\circ}\text{C}$		2.1	
	$T_A = 25\text{ }^{\circ}\text{C}$		2.0 ^{b, c}	
	$T_A = 70\text{ }^{\circ}\text{C}$		1.2 ^{b, c}	
Maximum Power Dissipation (Schottky)	$T_C = 25\text{ }^{\circ}\text{C}$		1.9	
	$T_C = 70\text{ }^{\circ}\text{C}$		1.2	
	$T_A = 25\text{ }^{\circ}\text{C}$		1.3 ^{b, c}	
	$T_A = 70\text{ }^{\circ}\text{C}$		0.9 ^{b, c}	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	$^{\circ}\text{C}$

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient (MOSFET) ^{b, d}	$t \leq 5 \text{ s}$	R_{thJA}	51	62.5	°C/W
Maximum Junction-to-Foot (Drain) (MOSFET)	Steady State	R_{thJF}	30	37	
Maximum Junction-to-Ambient (Schottky) ^{b, e}	$t \leq 5 \text{ s}$	R_{thJA}	73	90	
Maximum Junction-to-Foot (Drain) (Schottky)	Steady State	R_{thJF}	50	65	

Notes:

a. Based on $T_C = 25^\circ\text{C}$.

b. Surface Mounted on 1" x 1" FR4 board.

c. $t = 5 \text{ s}$.d. Maximum under Steady State conditions is 105°C/W .e. Maximum under Steady State conditions is 125°C/W .**SPECIFICATIONS $T_J = 25^\circ\text{C}$, unless otherwise noted**

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 20			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250 \mu\text{A}$		- 20		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			3		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$	- 0.6		- 1.5	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$			- 1	μA
		$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^\circ\text{C}$			- 10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq 5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 8			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -4.5 \text{ V}, I_D = -3.5 \text{ A}$		0.058	0.070	Ω
		$V_{GS} = -2.5 \text{ V}, I_D = -3.0 \text{ A}$		0.085	0.105	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10 \text{ V}, I_D = -3.5 \text{ A}$		10		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		480		pF
Output Capacitance	C_{oss}			132		
Reverse Transfer Capacitance	C_{rss}			55		
Total Gate Charge	Q_g	$V_{DS} = -10 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -5.0 \text{ A}$		9.7	14.5	nC
		$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_D = -4.5 \text{ A}$		4.5	7	
Gate-Source Charge	Q_{gs}			1.0		
Gate-Drain Charge	Q_{gd}			1.0		
Gate Resistance	R_g	$f = 1 \text{ MHz}$		7.5		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10 \text{ V}, R_L = 2.0 \Omega$ $I_D \cong -5.0 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 1 \Omega$		6	10	ns
Rise Time	t_r			54	85	
Turn-Off DelayTime	$t_{d(off)}$			19	30	
Fall Time	t_f			8	15	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10 \text{ V}, R_L = 2.0 \Omega$ $I_D \cong -5.0 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$		26	40	
Rise Time	t_r			80	120	
Turn-Off DelayTime	$t_{d(off)}$			20	30	
Fall Time	t_f			10	15	



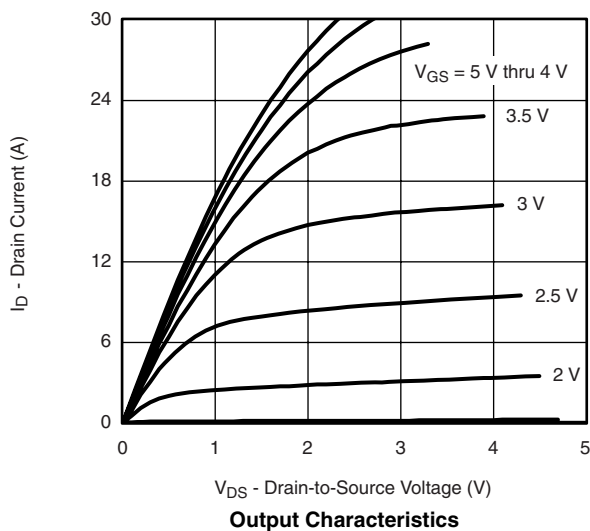
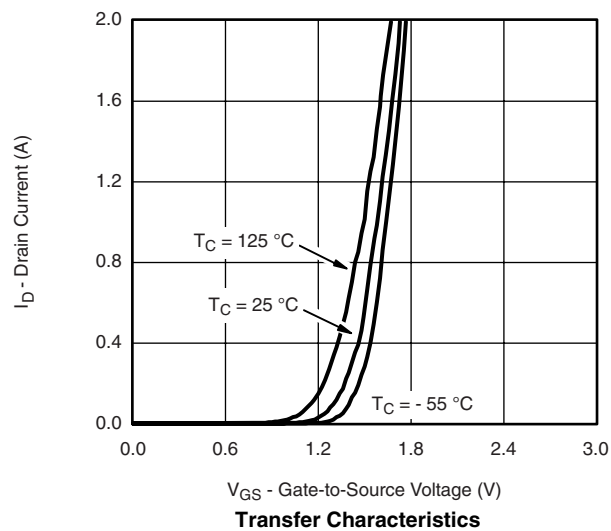
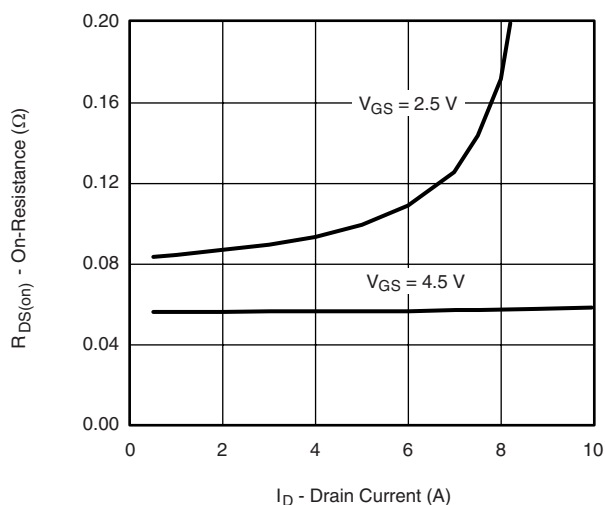
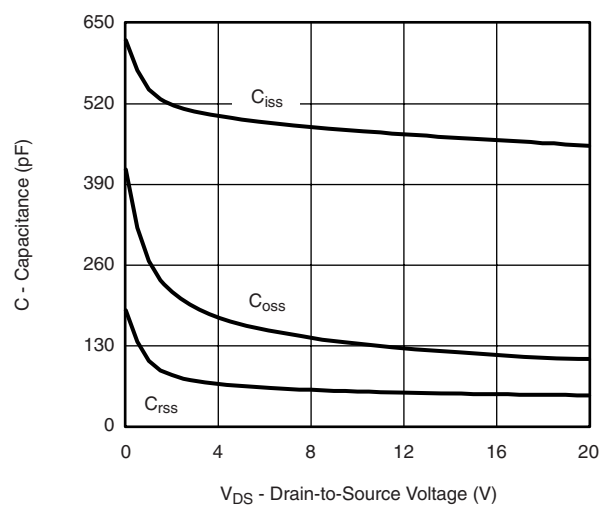
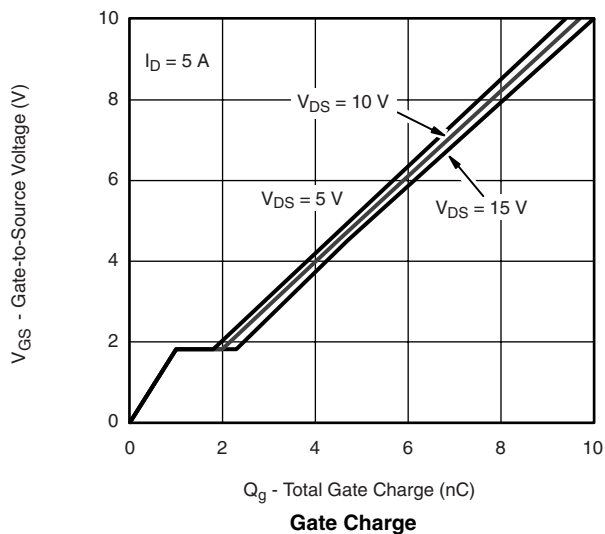
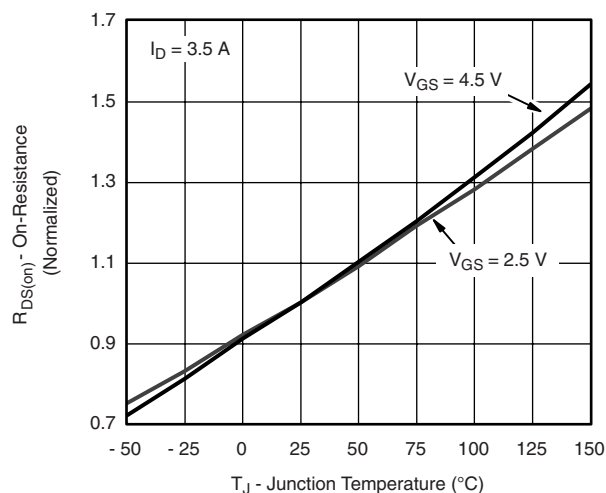
SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^{\circ}\text{C}$			- 2.7	A
Pulse Diode Forward Current	I_{SM}				- 20	
Body Diode Voltage	V_{SD}	$I_S = -1.0\text{ A}$, $V_{GS} = 0\text{ V}$		- 0.75	- 1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -3.5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25\text{ }^{\circ}\text{C}$		25	40	ns
Body Diode Reverse Recovery Charge	Q_{rr}			12	20	nC
Reverse Recovery Fall Time	t_a			9		ns
Reverse Recovery Rise Time	t_b			16		

Notes:

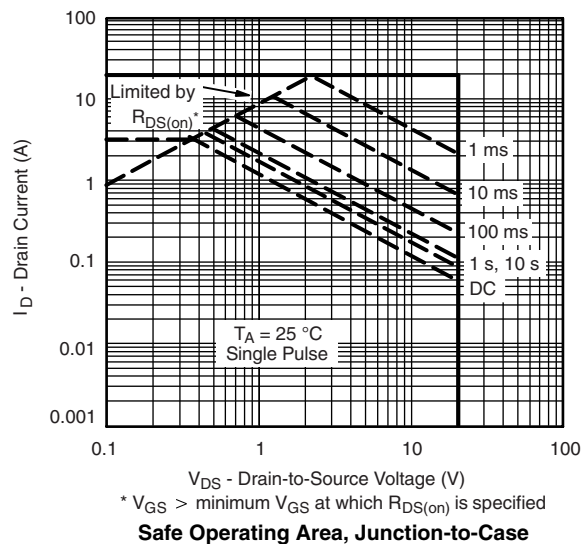
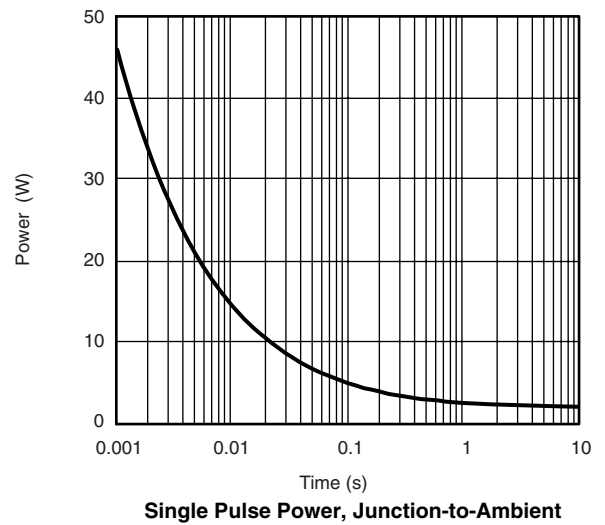
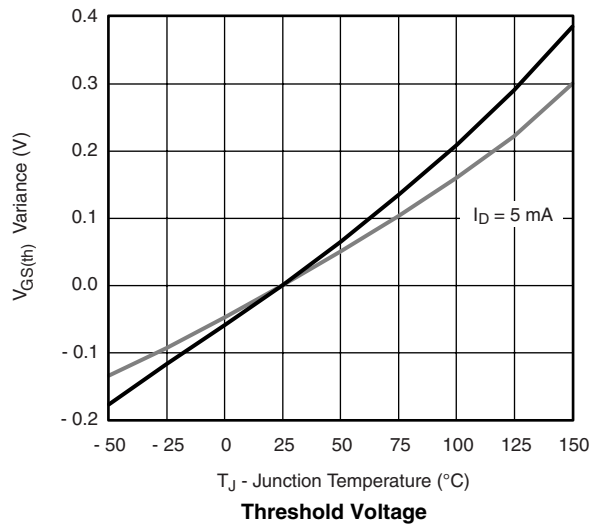
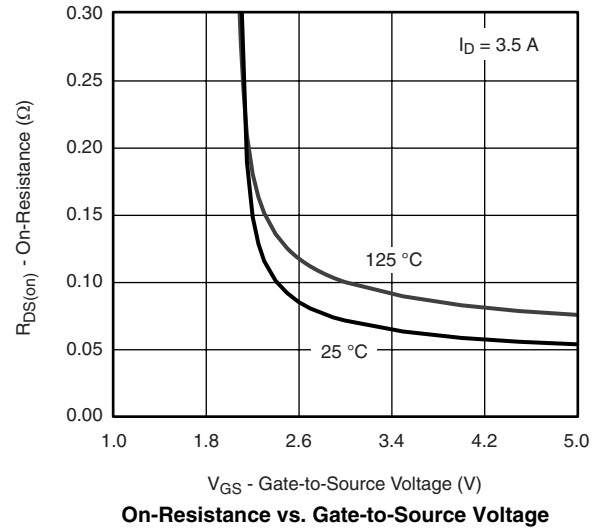
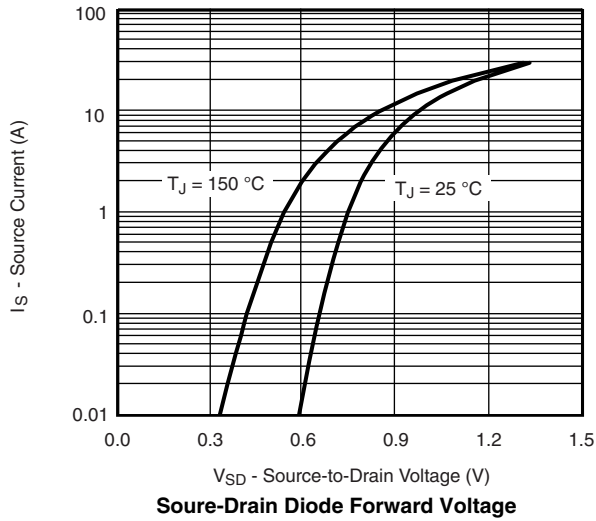
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

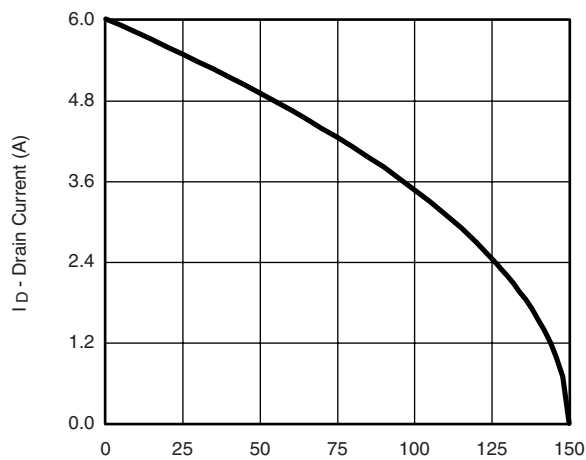
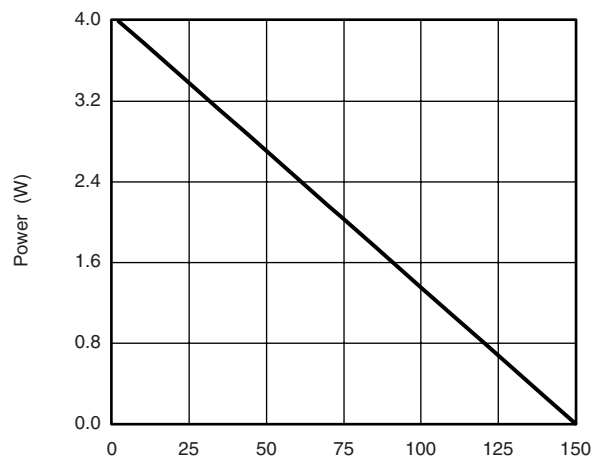
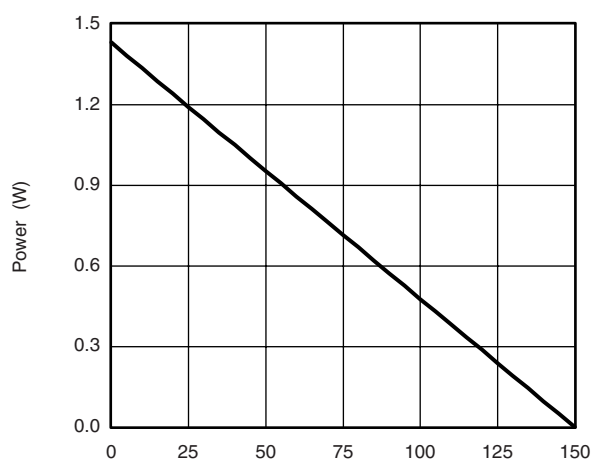
SCHOTTKY SPECIFICATIONS						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Forward Voltage Drop	V_F	$I_F = 1\text{ A}$		0.41	0.45	V
		$I_F = 1\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$		0.36	0.41	
Maximum Reverse Leakage Current	I_{rm}	$V_R = 5\text{ V}$		0.015	0.08	mA
		$V_R = 5\text{ V}$, $T_J = 85\text{ }^{\circ}\text{C}$		0.50	5.00	
		$V_R = 20\text{ V}$		0.02	0.10	
		$V_R = 20\text{ V}$, $T_J = 85\text{ }^{\circ}\text{C}$		0.7	7.00	
		$V_R = 20\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$		5	50	
Junction Capacitance	C_T	$V_R = 10\text{ V}$		60		pF

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

MOSFET TYPICAL CHARACTERISTICS $T_A = 25^\circ\text{C}$, unless otherwise noted

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current and Gate Voltage

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

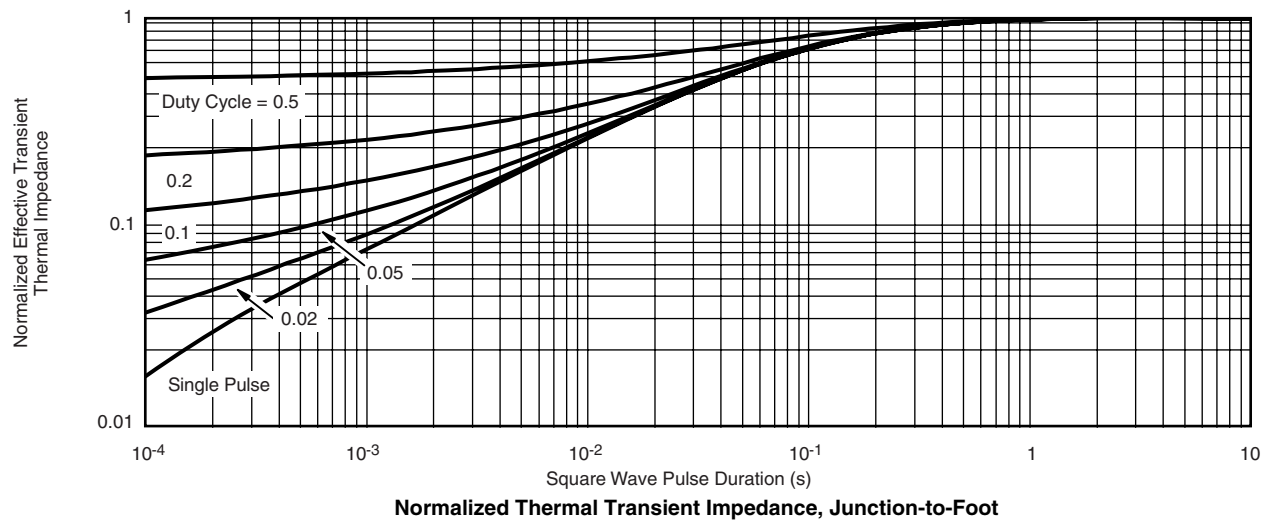
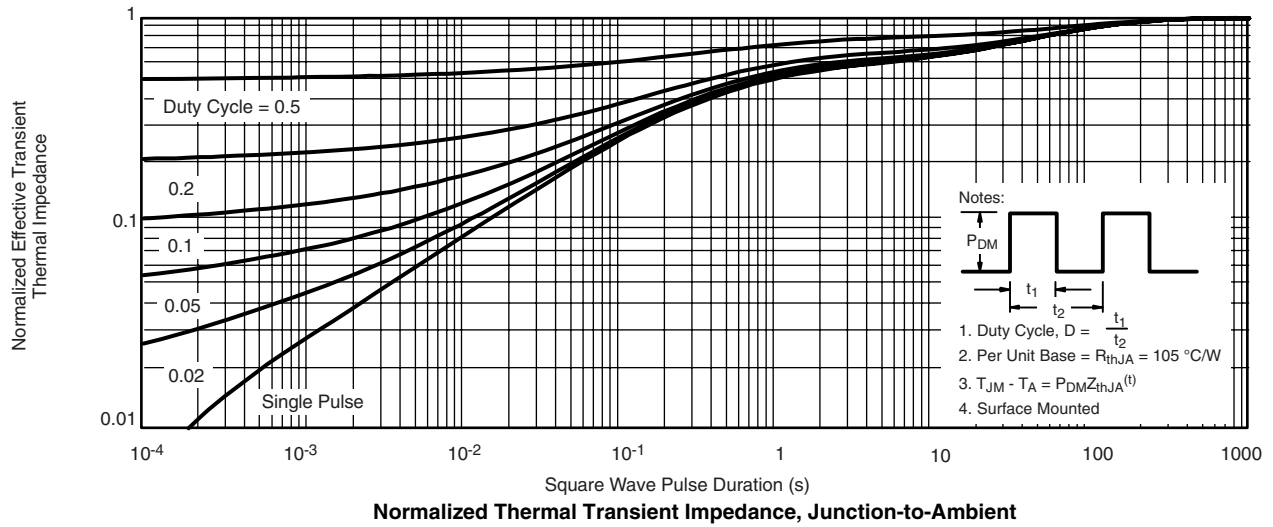
MOSFET TYPICAL CHARACTERISTICS $T_A = 25^\circ\text{C}$, unless otherwise noted

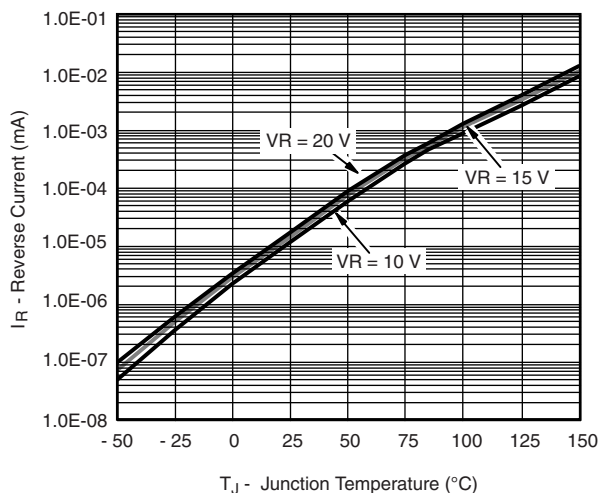
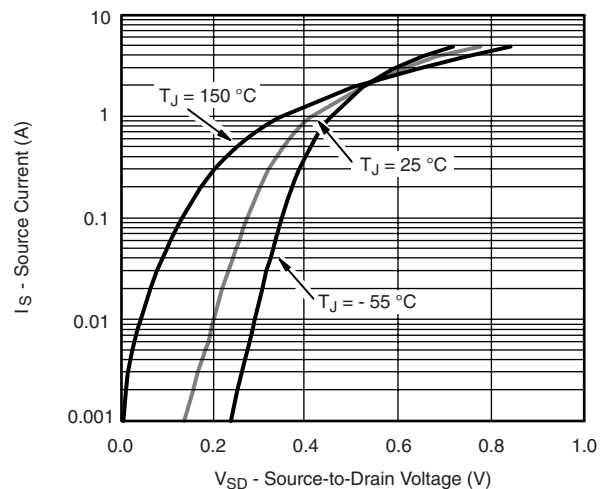
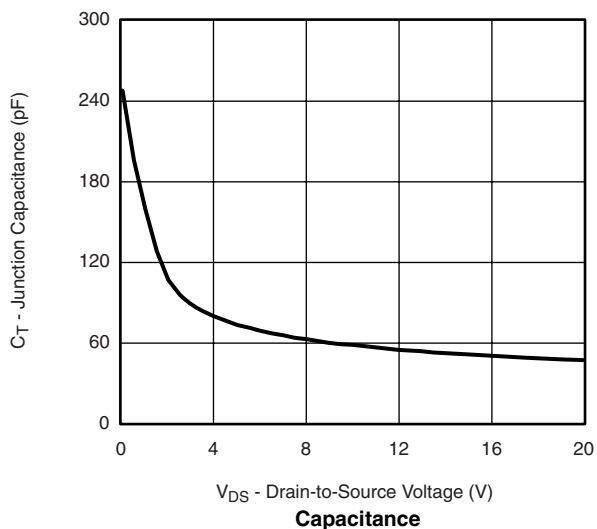
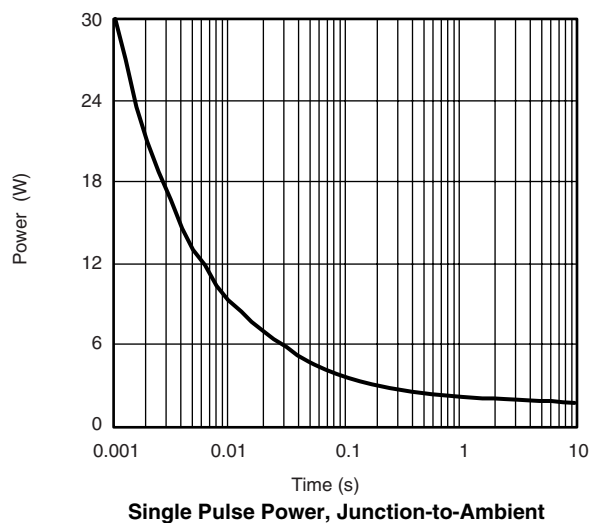


MOSFET TYPICAL CHARACTERISTICS $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted
 T_C - Case Temperature (°C)**Current Derating*** T_C - Case Temperature (°C)**Power Derating, Junction-to-Foot** T_A - Ambient Temperature (°C)**Power Derating, Junction-to-Ambient**

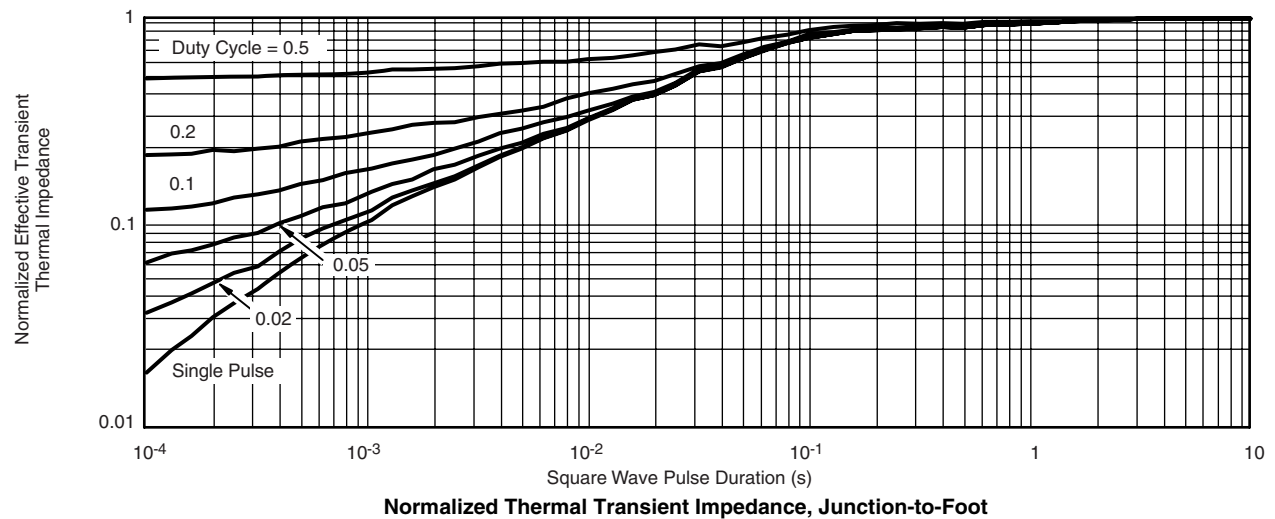
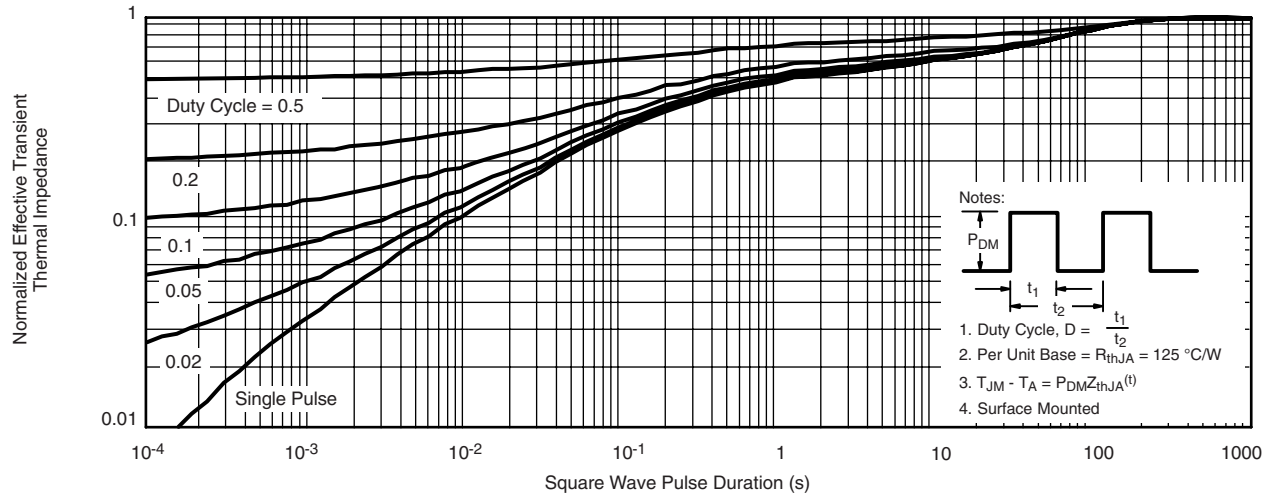
* The power dissipation P_D is based on $T_{J(max)} = 150\text{ }^{\circ}\text{C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

MOSFET TYPICAL CHARACTERISTICS $T_A = 25^\circ\text{C}$, unless otherwise noted



SCHOTTKY TYPICAL CHARACTERISTICS $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted

Reverse Current vs. Junction Temperature

Forward Diode Voltage

Capacitance

Single Pulse Power, Junction-to-Ambient

SCHOTTKY TYPICAL CHARACTERISTICS $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted



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